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N-Channel 20 V (D-S) MOSFET

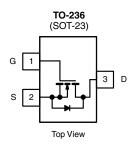
PRODUCT SUMMARY					
V _{DS} (V)	20				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.024				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 2.5 \text{ V}$	0.033				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 1.5 \text{ V}$	0.042				
I _D (A)	5.2				
Configuration	Single				

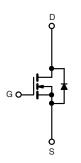
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- AEC-Q101 Qualified^c
- 100 % R_q and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



ROHS COMPLIANT HALOGEN FREE





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	(T _C = 25 °C, unles	ss otherwise noted	i)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	20		
Gate-Source Voltage		V _{GS}	± 8	V	
Continuous Drain Current	T _C = 25 °C	1	5.2		
Continuous Drain Current	T _C = 125 °C	Ι _D	3.5		
Continuous Source Current (Diode Conduction)		Is	2.5	Α	
Pulsed Drain Current ^a		I _{DM}	24		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	10		
Single Pulse Avalanche Energy	L = 0.1 min	E _{AS}	5	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	P _D	2	W	
Maximum Fower Dissipation-	T _C = 125 °C		0.6	VV	
Operating Junction and Storage Temperature	Range	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^b	R _{thJA}	175	°C/W
Junction-to-Foot (Drain)		R_{thJF}	R _{thJF} 75	

Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. Parametric verification ongoing.



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	1			L	·	ı	ı
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		20	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	0.4	0.6	1	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$		-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 20 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 20 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 20 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 4.5 V	$V_{DS} \ge 5 V$	10	-	-	Α
		V _{GS} = 4.5 V	I _D = 5 A	-	0.018	0.024	45 54 Ω 33 42 S
		$V_{GS} = 4.5 \text{ V}$	I _D = 5 A, T _J = 125 °C	-	-	0.045	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5V	I _D = 5 A, T _J = 175 °C	-	-	0.054	
		V _{GS} = 2.5 V	I _D = 4 A	-	0.027	0.033	
		V _{GS} = 1.5 V	I _D = 2 A	-	0.034	0.042	
Forward Transconductanceb	9fs	V _{DS} = 15 V, I _D = 5 A		-	27	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	387	485	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 10 V, f = 1 MHz	-	80	100	pF
Reverse Transfer Capacitance	C _{rss}			-	37	46	
Total Gate Charge ^c	Qg			-	4.5	8.5	
Gate-Source Charge ^c	Q_{gs}	$V_{GS} = 4.5 \text{ V}$	$V_{DS} = 10 \text{ V}, I_{D} = 5 \text{ A}$	-	0.4	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	0.7	-	
Gate Resistance	R _g	f = 1 MHz		6	12	18	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	7	11	
Rise Time ^c	t _r	$V_{DD} = 10 \text{ V, R}_{I} = 2.5 \Omega$		-	8	12	ne
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 4 \text{ A}, \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	$I_{\rm GEN} = 4.5 \text{V}, \text{R}_{\rm g} = 1 \Omega$	-	21	32	ns
Fall Time ^c	t _f			-	9	14	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	24	Α
Forward Voltage	V _{SD}	I _F =	= 5 A, V _{GS} = 0 V	-	0.75	1.2	V

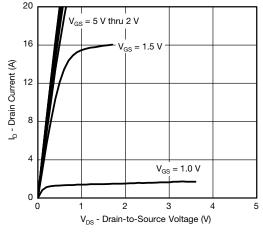
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

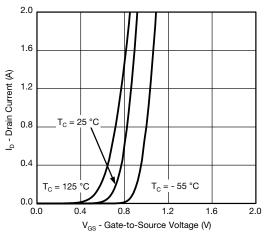
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



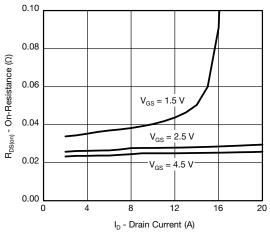
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



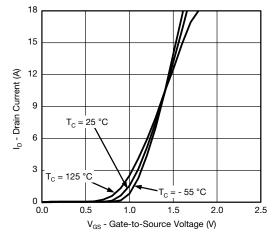
Output Characteristics



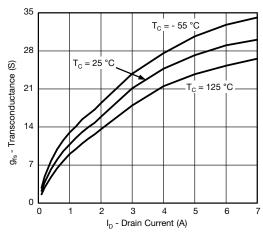
Transfer Characteristics



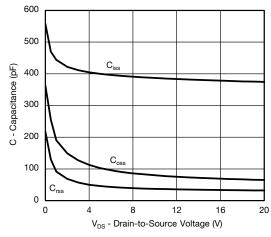
On-Resistance vs. Drain Current



Transfer Characteristics



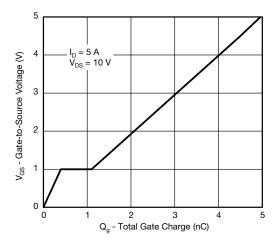
Transconductance



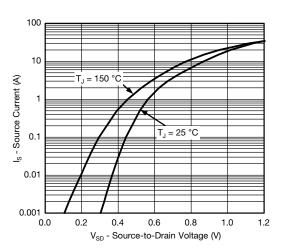
Capacitance



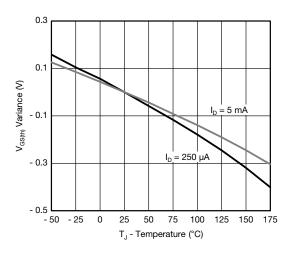
TYPICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}\text{C}$, unless otherwise noted)



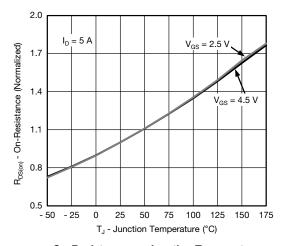
Gate Charge



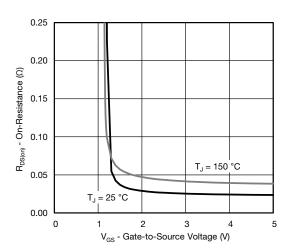
Source Drain Diode Forward Voltage



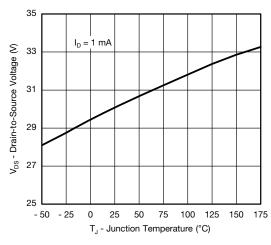
Threshold Voltage



On-Resistance vs. Junction Temperature



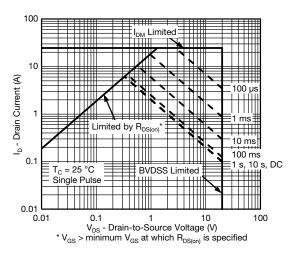
On-Resistance vs. Gate-to-Source Voltage



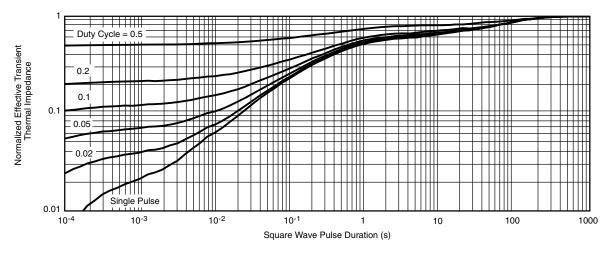
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



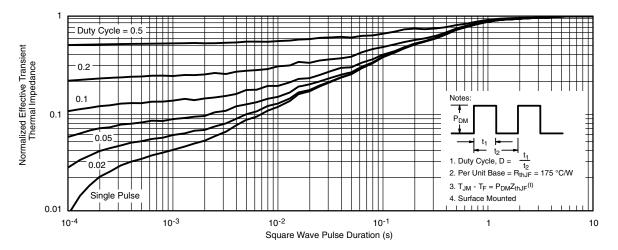
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

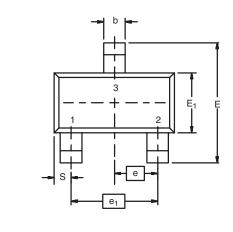
Note

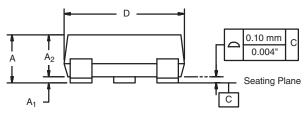
- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

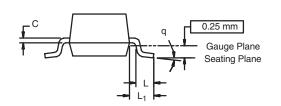
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



SOT-23 (TO-236): 3-LEAD





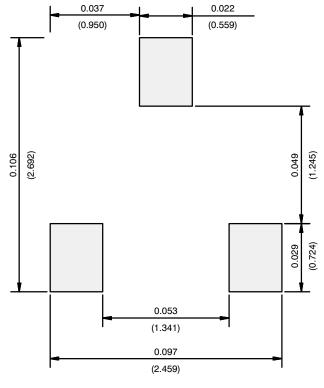


Dim	MILLIM	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.074	8 Ref	
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025	5 Ref	
S	0.50 Ref		0.020) Ref	
q	3°	8°	3°	8°	

DWG: 5479



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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